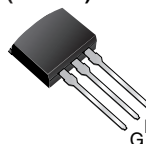


Power MOSFET

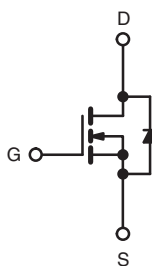
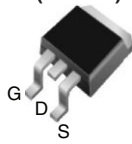
PRODUCT SUMMARY

V_{DS} (V)	500	
$R_{DS(on)}$ (Max.) (Ω)	$V_{GS} = 10\text{ V}$	1.40
Q_g (Max.) (nC)	24	
Q_{gs} (nC)	6.3	
Q_{gd} (nC)	11	
Configuration	Single	

I²PAK
(TO-262)



D²PAK
(TO-263)



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} specified
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High speed power switching

TYPICAL SMPS TOPOLOGIES

- Two Transistor Forward
- Half Bridge and Full Bridge

ORDERING INFORMATION

Package	D ² PAK (TO-263)	D ² PAK (TO-263)	I ² PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHF830AS-GE3	SiHF830ASTRL-GE3 ^a	SiHF830AL-GE3 ^a
Lead (Pb)-free	IRF830ASPbF	IRF830ASTRLPbF ^a	IRF830ALPbF
	SiHF830AS-E3	SiHF830ASTL-E3 ^a	SiHF830AL-E3

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A
		$T_C = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current ^{a, e}	I_{DM}	20	
Linear Derating Factor		0.59	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ^{b, e}	E_{AS}	230	mJ
Avalanche Current ^a	I_{AR}	5.0	A
Repetitive Avalanche Energy ^a	E_{AR}	7.4	mJ
Maximum Power Dissipation		$T_A = 25\text{ }^\circ\text{C}$	W
		$T_C = 25\text{ }^\circ\text{C}$	
Peak Diode Recovery dV/dt ^{c, e}	dV/dt	5.3	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 18\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 5.0\text{ A}$ (see fig. 12).
- $I_{SD} \leq 5.0\text{ A}$, $dI/dt \leq 370\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.
- Uses SiHF830A data and test conditions.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mounted, Steady-State) ^a	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		500	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA ^d		-	0.60	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.5	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 30 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 400 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.0 A ^b	-	-	1.4	Ω
Forward Transconductance	g _{fs}	V _{DS} = 50 V, I _D = 3.0 A ^d		2.8	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5 ^d		-	620	-	pF
Output Capacitance	C _{oss}			-	93	-	
Reverse Transfer Capacitance	C _{rss}			-	4.3	-	
Output Capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 1.0 V, f = 1.0 MHz	-	886	-	
			V _{DS} = 400 V, f = 1.0 MHz	-	27	-	
Effective Output Capacitance	C _{oss eff.}		V _{DS} = 0 V to 400 V ^{c, d}	-	39	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 5.0 A, V _{DS} = 400 V, see fig. 6 and 13 ^{b, d}	-	-	24	nC
Gate-Source Charge	Q _{gs}			-	-	6.3	
Gate-Drain Charge	Q _{gd}			-	-	11	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 250 V, I _D = 5.0 A, R _g = 14 Ω, R _D = 49 Ω, see fig. 10 ^{b, d}		-	10	-	ns
Rise Time	t _r			-	21	-	
Turn-Off Delay Time	t _{d(off)}			-	21	-	
Fall Time	t _f			-	15	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	5.0	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	20	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = 5.0 A, V _{GS} = 0 V ^b		-	-	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 5.0 A, dI/dt = 100 A/μs ^{b, d}		-	430	650	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	2.0	3.0	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS} .
- Uses SiHF830A data and test conditions.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

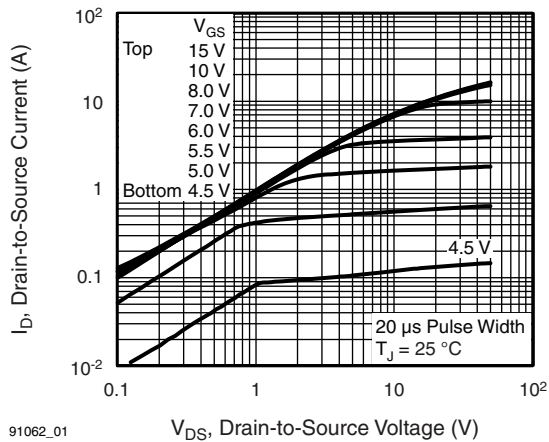


Fig. 1 - Typical Output Characteristics

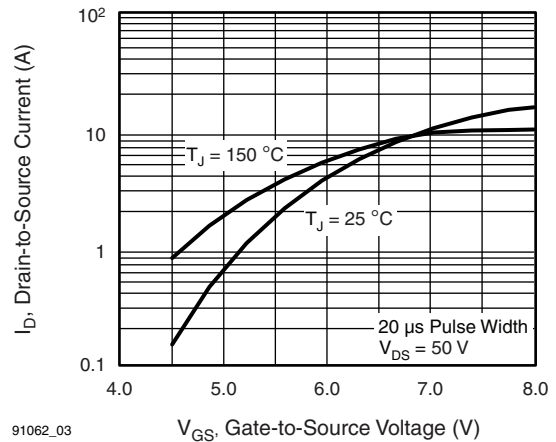


Fig. 3 - Typical Transfer Characteristics

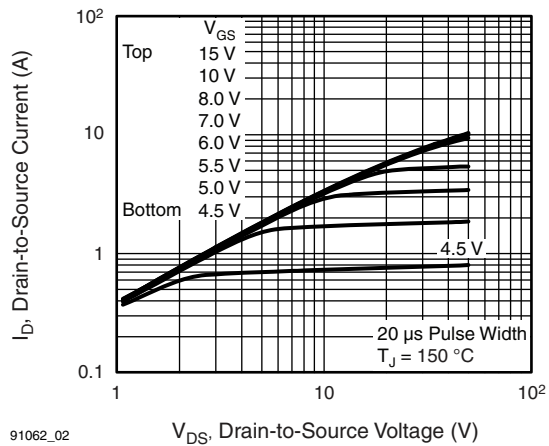


Fig. 2 - Typical Output Characteristics

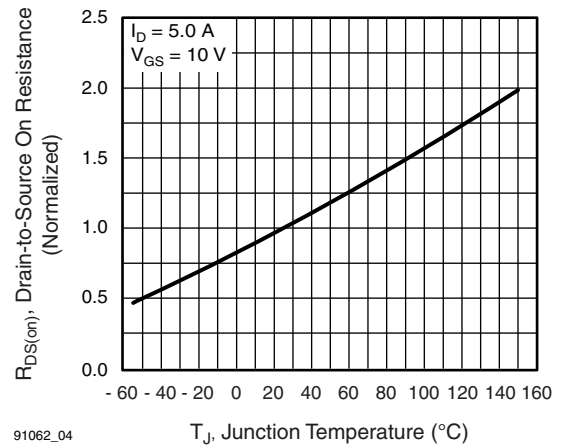
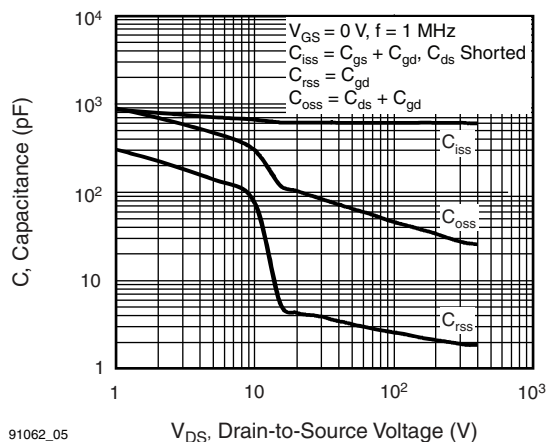
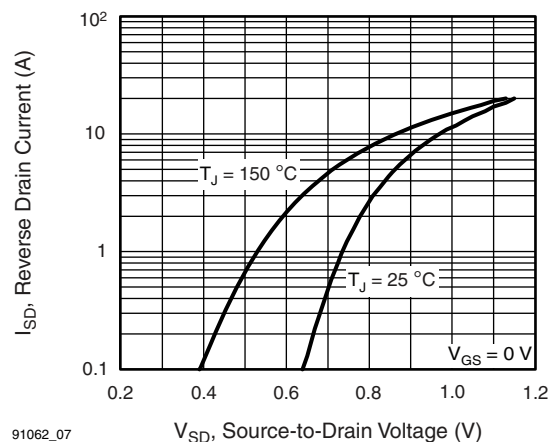


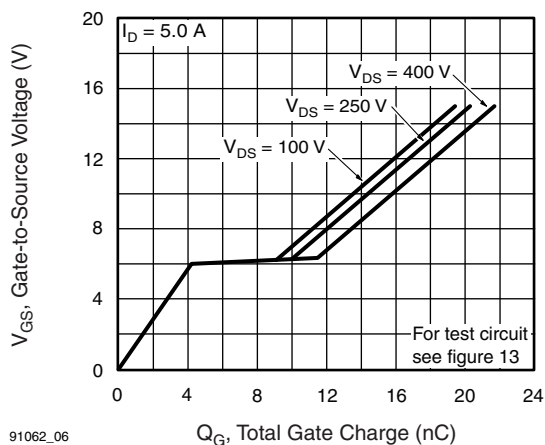
Fig. 4 - Normalized On-Resistance vs. Temperature



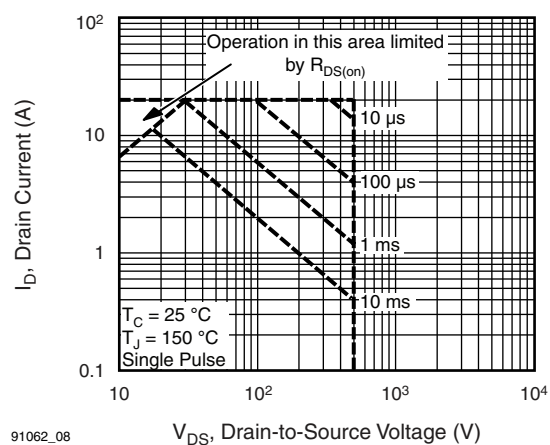
91062_05



91062_07



91062_06



91062_08

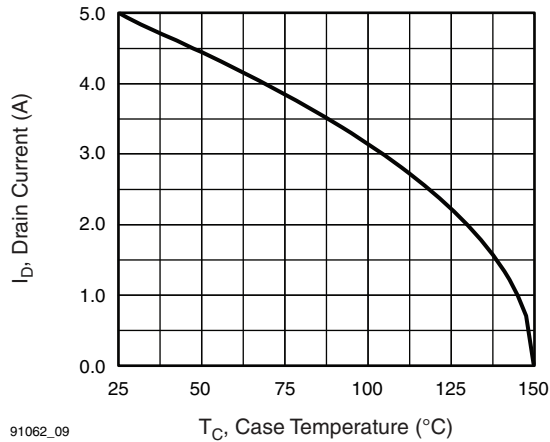


Fig. 9 - Maximum Drain Current vs. Case Temperature

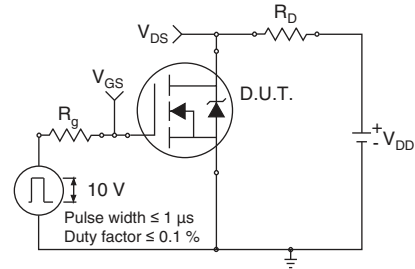


Fig. 10a - Switching Time Test Circuit

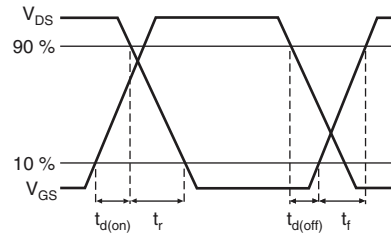


Fig. 10b - Switching Time Waveforms

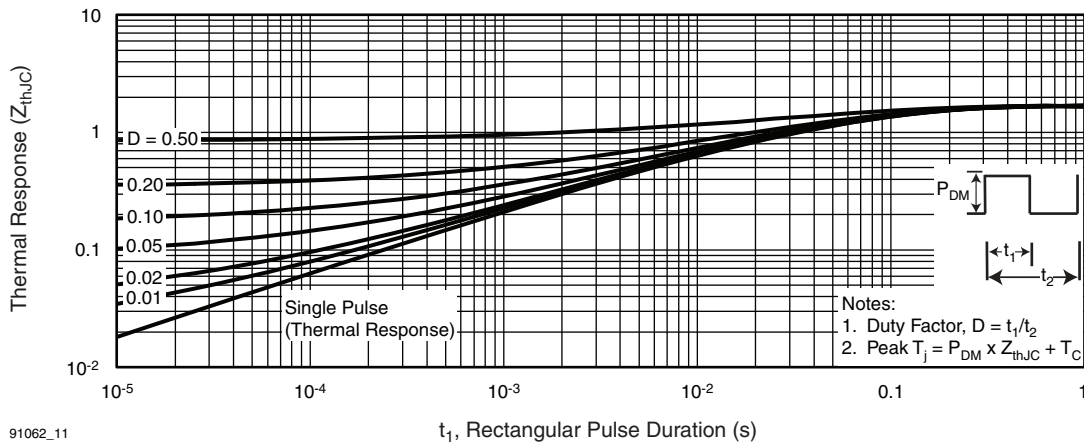


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

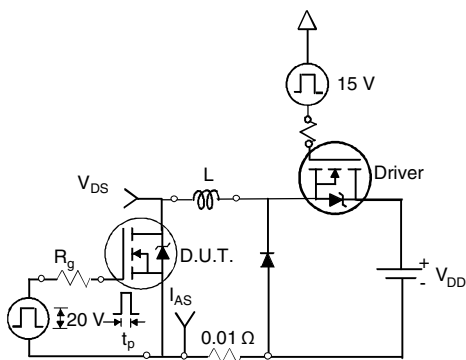


Fig. 12a - Unclamped Inductive Test Circuit

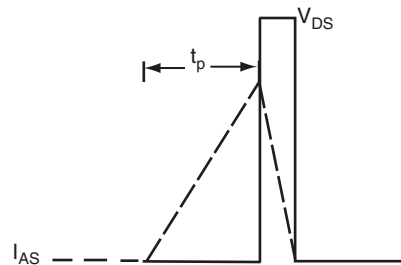


Fig. 12b - Unclamped Inductive Waveforms

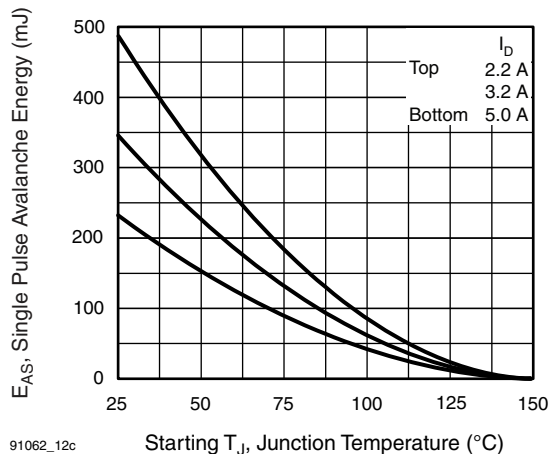


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

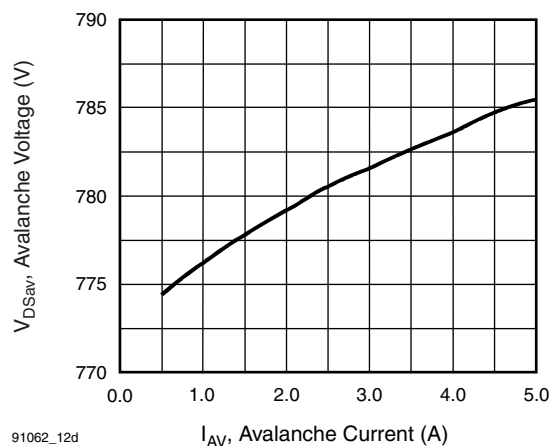


Fig. 12d - Basic Gate Charge Waveform

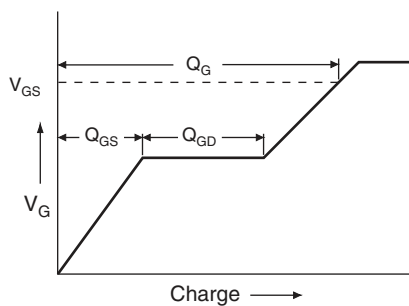


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

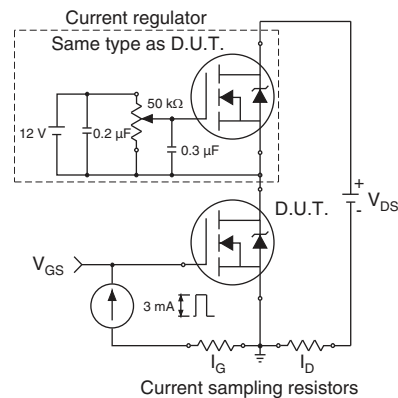
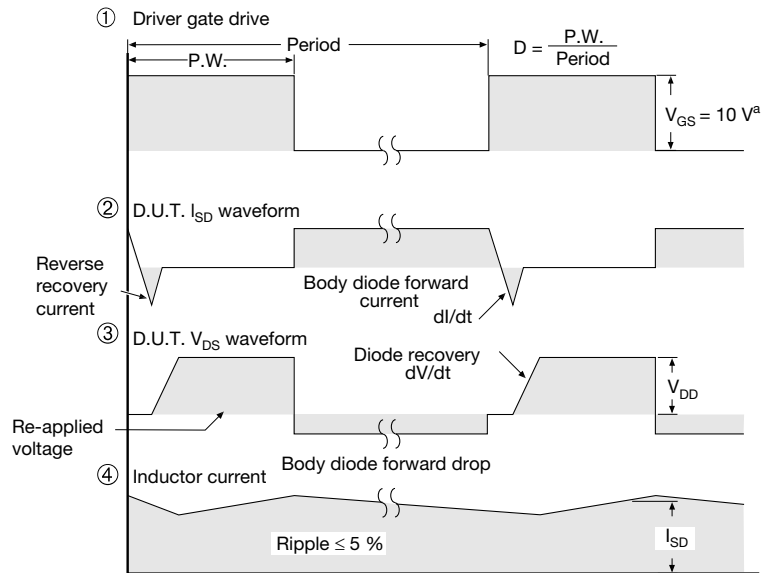
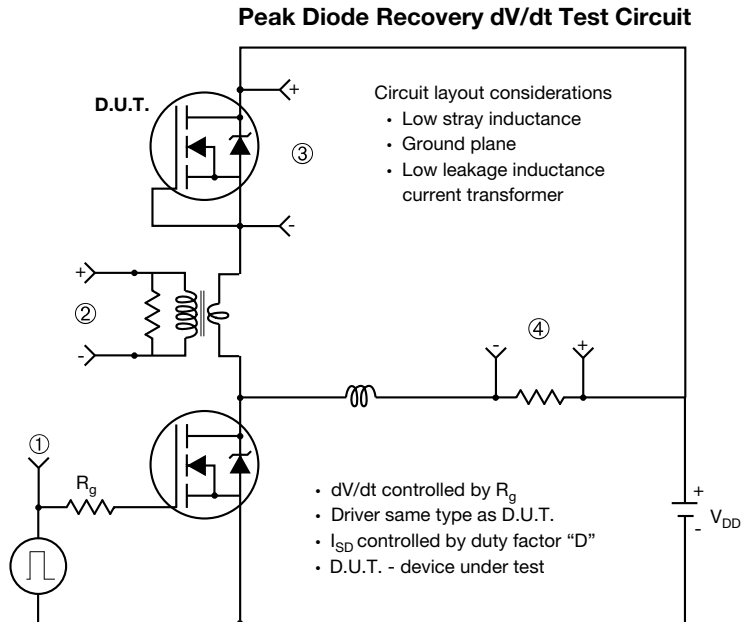


Fig. 13b - Gate Charge Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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